

10th International Conference on Radiation Effects on Semiconductor Materials, Detectors and Devices

Thursday, 9 October 2014

Electronics (11:20 - 13:00)

time	[id] title	presenter
11:20	[50] Monolithic active pixel sensor for ionizing radiation using 180nm HV-SOI process	HEMPEREK, Thomas
11:40	[19] Measurements Results on a 180nm SOI Monolithic Active Pixel Sensor	FERNANDEZ PEREZ, Sonia
12:00	[51] Test-beam results on a monolithic pixel sensor in the 0.18um Tower-Jazz technology with high resistivity epitaxial layer	MATTIAZZO, Serena
12:20	[33] High Intensity Irradiation Influence on Gain, Noise and Offset Uniformity of a Pixel Detector Readout designed in 130nm CMOS	SATŁAWA, Tadeusz
12:40	[38] Investigation of total ionizing dose effect and displacement damage in 65 nm CMOS transistors exposed to 3 MeV proton	BISELLO, Dario Dr DING, LILI Dr BAGATIN, Marta